IN THE CLAIMS:

Please amend Claims 1, 6, 11 and 12, as shown.

1. (Currently Amended): A simulation method for simulating an amount of occurrence of local flare which occurs in an exposure process in manufacturing a semiconductor device <u>for use in optical corrections to obtain a more accurate optical image</u>, comprising the steps of:

dividing a layout of a photo mask into a plurality of areas,

calculating an average value of light intensity in each of the areas, and

estimating the amount of occurrence of local flare in each of the areas on the basis of each of the average values<u>, wherein</u>

<u>when a circular-shaped light source is used, the average value of light intensity</u>

$$\bar{I} = \sum_{k=1}^{N} F_k S_k S_k^*$$ <u>... and F$_k$ is a weighting factor of diffracted light and S$_k$ is the amplitude of the</u>

<u>diffracted light, and</u> $F_k = A_k / (\sigma^2 \pi)$ <u>where A$_k$ is the area shared between a circle C having a radius NA, the numerical aperture of the lens, and a circle S$_k$ having a radius of the light source with respect to NA, and σ is the radius of the circular shaped light source with respect to NA, and</u>

<u>when a ring-shaped light source is used, F$_k$ = A$_k$/ ($\sigma_2^2 \pi - \sigma_1^2 \pi$) where σ_1 is the inside radius and σ_2 is the outside radius of the ring-shaped light source with respect to NA.</u>

2. (Original): The simulation method according to claim 1, wherein

each of the average values is subjected to smoothing processing, a smoothed average value is multiplied by a first multiplier, and an obtained value is evaluated as the amount of occurrence of local flare in each of the areas.

3. (Original): The simulation method according to claim 1, wherein

when the average value of light intensity in each of the areas is calculated, diffracted light is calculated by a Fourier transformed image of each of the areas of the layout, and the average value is calculated by multiplying the light intensity of the diffracted light passing through a projection lens by a second multiplier.

4. (Original): The simulation method according to claim 1, wherein

each of the values evaluated as the amount of occurrence of local flare is added to the light intensity in order to simulate an optical image.

5. (Original): The simulation method according to claim 1, wherein

each of the values evaluated as the amount of occurrence of local flare is used in optical proximity correction.

6. (Currently Amended): Simulation equipment for simulating an amount of occurrence of local flare which occurs in an exposure process in manufacturing a semiconductor device <u>for use in optical corrections to obtain a more accurate optical image</u>, comprising:

division unit for dividing a layout of a photo mask into a plurality of areas;

average light intensity value calculation unit for calculating an average value of light intensity in each of the areas, wherein

the amount of occurrence of local flare in each of the areas is estimated on the basis of each of the average values, and

when a circular-shaped light source is used, the average value of light intensity $\bar{I} = \sum_{k=1}^{N} F_k S_k S_k^*$ ... and F_k is a weighting factor of diffracted light and S_k is the amplitude of the diffracted light, and $F_k = A_k / (\sigma^2 \pi)$ where A_k is the area shared between a circle C having a radius NA, the numerical aperture of the lens, and a circle S_k having a radius of the light source with respect to NA, and σ is the radius of the circular shaped light source with respect to NA, and

when a ring-shaped light source is used, $F_k = A_k / \sigma_2^2 \pi - \sigma_1^2 \pi)$ where σ_1 is the inside radius and σ_2 is the outside radius of the ring-shaped light source with respect to NA.

7. (Original): The simulation equipment according to claim 6 further comprising:

smoothing unit for subjecting the calculated average value to smoothing processing, and multiplication unit for multiplying the smoothed average value by a first multiplier,

wherein each obtained value is evaluated as the amount of occurrence of local flare in each of the areas.

8. (Original): The simulation equipment according to claim 6, wherein

when the average value of light intensity in each of the areas is calculated, diffracted light is calculated by a Fourier transformed image of each of the areas of the layout, and the average

value is calculated by multiplying the light intensity of the diffracted light passing through a projection lens by a second multiplier.

9. (Original): The simulation equipment according to claim 6, wherein

each of the values evaluated as the amount of occurrence of local flare is added to the light intensity in order to simulate an optical image.

10. (Original): The simulation equipment according to claim 6, wherein

each of the values evaluated as the amount of occurrence of local flare is used in optical proximity correction.

11. (Currently Amended): A computer-readable storage medium on which a computer program for use in optical corrections to obtain a more accurate optical image for simulating an amount of occurrence of local flare which occurs in an exposure process in manufacturing a semiconductor is stored, said computer program comprising:

a computer-readable program code means for executing a step of dividing a layout of a photo mask into a plurality of areas;

a computer-readable program code means for executing a step of calculating an average value of light intensity in each of the areas; and

a computer-readable program code means for executing a step of simulating and estimating an amount of occurrence of local flare in each of the areas on the basis of each of the average values, ~~the local flare occurring in an exposure process in manufacturing a~~

~~semiconductor device~~ for use in optical corrections to obtain a more accurate optical image, wherein

when a circular-shaped light source is used, the average value of light intensity

$$\bar{I} = \sum_{k=1}^{N} F_k S_k S_k^* \dots$$ and F_k is a weighting factor of diffracted light and S_k is the amplitude of the

diffracted light, and $F_k = A_k / (\sigma^2 \pi)$ where A_k is the area shared between a circle C having a

radius NA, the numerical aperture of the lens, and a circle S_k having a radius of the light source

with respect to NA, and σ is the radius of the circular shaped light source with respect to NA,

and

when a ring-shaped light source is used, $F_k = A_k / \sigma_2^2 \pi - \sigma_1^2 \pi)$ where σ_1 is the inside

radius and σ_2 is the outside radius of the ring-shaped light source with respect to NA.

12. (Currently Amended): A computer program product for use in optical corrections to

obtain a more accurate optical image for simulating an amount of occurrence of local flare which

occurs in an exposure process in manufacturing a semiconductor, comprising:

a computer-readable program code means for executing a step of dividing a layout of a

photo mask into a plurality of areas; a computer-readable program code means for executing a

step of calculating an average value of light intensity in each of the areas; and

a computer-readable program code means for executing a step of simulating and

estimating an amount of occurrence of local flare in each of the areas on the basis of each of the

average values, ~~the local flare occurring in an exposure process in manufacturing a~~

~~semiconductor device~~ for use in optical corrections to obtain a more accurate optical image, wherein

when a circular-shaped light source is used, the average value of light intensity $\bar{I} = \sum_{k=1}^{N} F_k S_k S_k^*$ ... and F_k is a weighting factor of diffracted light and S_k is the amplitude of the diffracted light, and $F_k = A_k / (\sigma^2 \pi)$ where A_k is the area shared between a circle C having a radius NA, the numerical aperture of the lens, and a circle S_k having a radius of the light source with respect to NA, and σ is the radius of the circular shaped light source with respect to NA, and

when a ring-shaped light source is used, $F_k = A_k / \sigma_2^2 \pi - \sigma_1^2 \pi)$ where σ_1 is the inside radius and σ_2 is the outside radius of the ring-shaped light source with respect to NA.